

NTGS3441T1

Power MOSFET 1 Amp, 20 Volts

P-Channel TSOP-6

Features

- Ultra Low $R_{DS(on)}$
- Higher Efficiency Extending Battery Life
- Miniature TSOP-6 Surface Mount Package
- Pb-Free Package is Available

Applications

- Power Management in Portable and Battery-Powered Products, i.e.: Cellular and Cordless Telephones, and PCMCIA Cards

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	-20	V
Gate-to-Source Voltage – Continuous	V_{GS}	± 8.0	V
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	244	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_d	0.5	W
Drain Current – Continuous @ $T_A = 25^\circ\text{C}$	I_D	-1.65	A
– Pulsed Drain Current ($T_p < 10 \mu\text{s}$)	I_{DM}	-10	A
Thermal Resistance Junction-to-Ambient (Note 2)	$R_{\theta JA}$	128	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_d	1.0	W
Drain Current – Continuous @ $T_A = 25^\circ\text{C}$	I_D	-2.35	A
– Pulsed Drain Current ($T_p < 10 \mu\text{s}$)	I_{DM}	-14	A
Thermal Resistance Junction-to-Ambient (Note 3)	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_d	2.0	W
Drain Current – Continuous @ $T_A = 25^\circ\text{C}$	I_D	-3.3	A
– Pulsed Drain Current ($T_p < 10 \mu\text{s}$)	I_{DM}	-20	A
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$
Maximum Lead Temperature for Soldering Purposes for 10 Seconds	T_L	260	$^\circ\text{C}$

1. Minimum FR-4 or G-10PCB, operating to steady state.
2. Mounted onto a 2" square FR-4 board (1" sq. 2 oz. cu. 0.06" thick single sided), operating to steady state.
3. Mounted onto a 2" square FR-4 board (1" sq. 2 oz. cu. 0.06" thick single sided), $t < 5.0$ seconds.

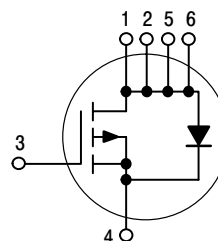


ON Semiconductor®

<http://onsemi.com>

**1 AMPERE
20 VOLTS**
 $R_{DS(on)} = 90 \text{ m}\Omega$

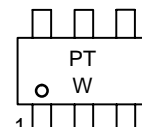
P-Channel



MARKING DIAGRAM

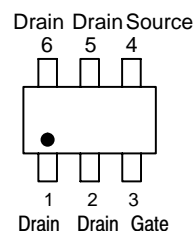


**TSOP-6
CASE 318G
STYLE 1**



PT = Device Code
W = Work Week

PIN ASSIGNMENT



ORDERING INFORMATION

Device	Package	Shipping†
NTGS3441T1	TSOP-6	3000 / Tape & Reel
NTGS3441T1G	TSOP-6 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTGS3441T1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Notes 4 & 5)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain–Source Breakdown Voltage (V _{GS} = 0 Vdc, I _D = –10 μA)	V _{(BR)DSS}	–20	–	–		Vdc
Zero Gate Voltage Drain Current (V _{GS} = 0 Vdc, V _{DS} = –20 Vdc, T _J = 25°C) (V _{GS} = 0 Vdc, V _{DS} = –20 Vdc, T _J = 70°C)	I _{DSS}	– –	– –	–1.0 –5.0		μAdc
Gate–Body Leakage Current (V _{GS} = –8.0 Vdc, V _{DS} = 0 Vdc)	I _{GSS}	–	–	–100		nAdc
Gate–Body Leakage Current (V _{GS} = +8.0 Vdc, V _{DS} = 0 Vdc)	I _{GSS}	–	–	100		nAdc
ON CHARACTERISTICS						
Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = –250 μAdc)	V _{GS(th)}	–0.45	–1.05	–1.50		Vdc
Static Drain–Source On–State Resistance (V _{GS} = –4.5 Vdc, I _D = –3.3 Adc) (V _{GS} = –2.5 Vdc, I _D = –2.9 Adc)	R _{DS(on)}	– –	0.069 0.117	0.090 0.135		Ω
Forward Transconductance (V _{DS} = –10 Vdc, I _D = –3.3 Adc)	g _{FS}	–	6.8	–		mhos
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V _{DS} = –5.0 Vdc, V _{GS} = 0 Vdc, f = 1.0 MHz)	C _{iss}	–	480	–	pF
Output Capacitance		C _{oss}	–	265	–	pF
Reverse Transfer Capacitance		C _{rss}	–	100	–	pF
SWITCHING CHARACTERISTICS						
Turn–On Delay Time	(V _{DD} = –20 Vdc, I _D = –1.6 Adc, V _{GS} = –4.5 Vdc, R _g = 6.0 Ω)	t _{d(on)}	–	13	25	ns
Rise Time		t _r	–	23.5	45	ns
Turn–Off Delay Time		t _{d(off)}	–	27	50	ns
Fall Time		t _f	–	24	45	ns
Total Gate Charge	(V _{DS} = –10 Vdc, V _{GS} = –4.5 Vdc, I _D = –3.3 Adc)	Q _{tot}	–	6.2	14	nC
Gate–Source Charge		Q _{gs}	–	1.3	–	nC
Gate–Drain Charge		Q _{gd}	–	2.5	–	nC
BODY–DRAIN DIODE RATINGS						
Diode Forward On–Voltage	(I _S = –1.6 Adc, V _{GS} = 0 Vdc)	V _{SD}	–	–0.88	–1.2	Vdc
Diode Forward On–Voltage	(I _S = –3.3 Adc, V _{GS} = 0 Vdc)	V _{SD}	–	–0.98	–	Vdc
Reverse Recovery Time	(I _S = –1.6 Adc, dI _S /dt = 100 A/μs)	t _{rr}	–	30	60	ns

4. Indicates Pulse Test: P.W. = 300 μsec max, Duty Cycle = 2%.

5. Handling precautions to protect against electrostatic discharge is mandatory.

TYPICAL ELECTRICAL CHARACTERISTICS

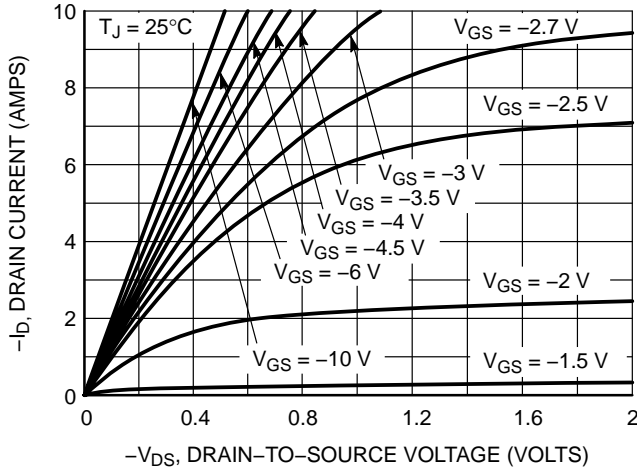


Figure 1. On-Region Characteristics

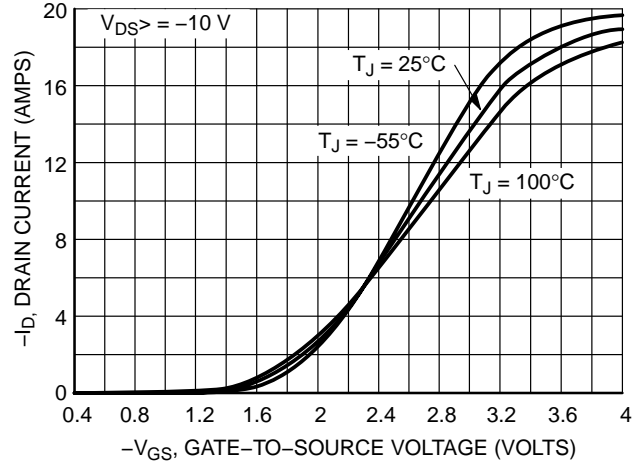


Figure 2. Transfer Characteristics

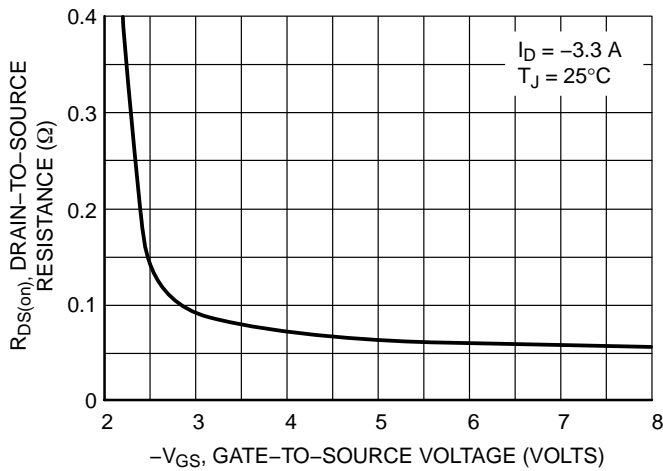


Figure 3. On-Resistance vs. Gate-to-Source Voltage

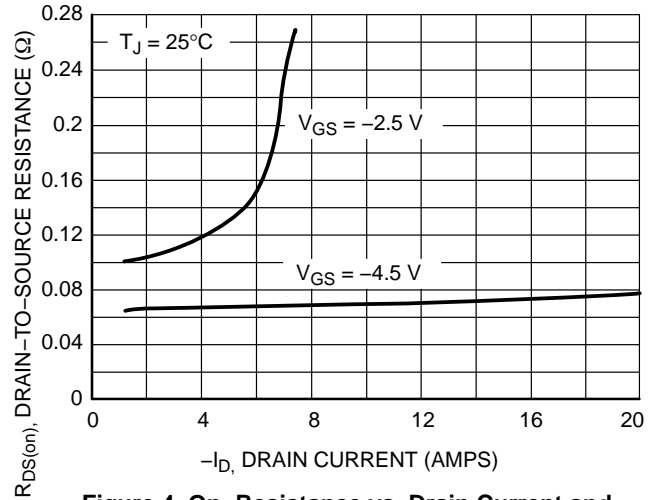


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

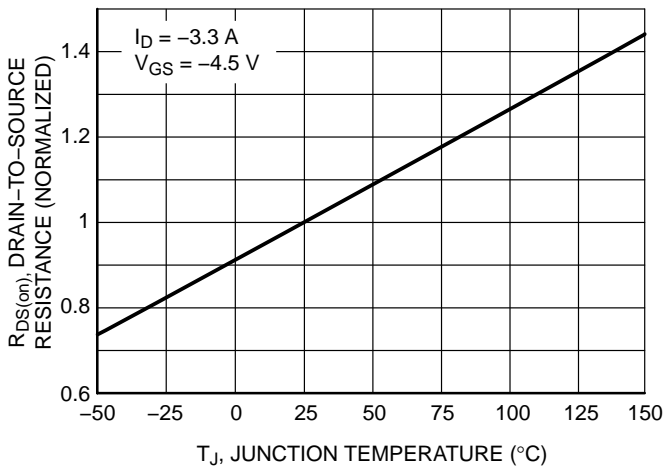


Figure 5. On-Resistance Variation with Temperature

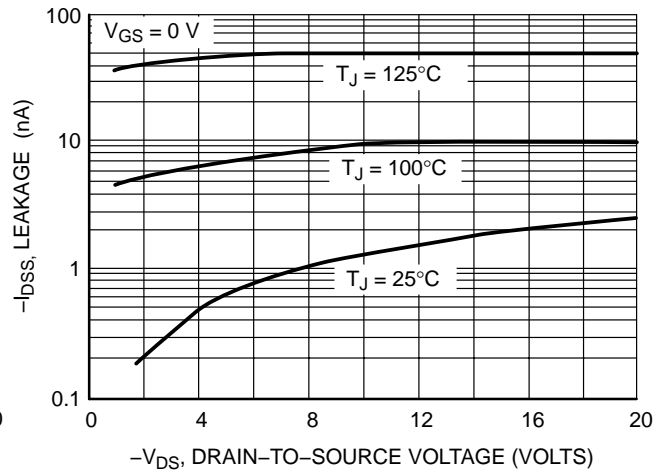
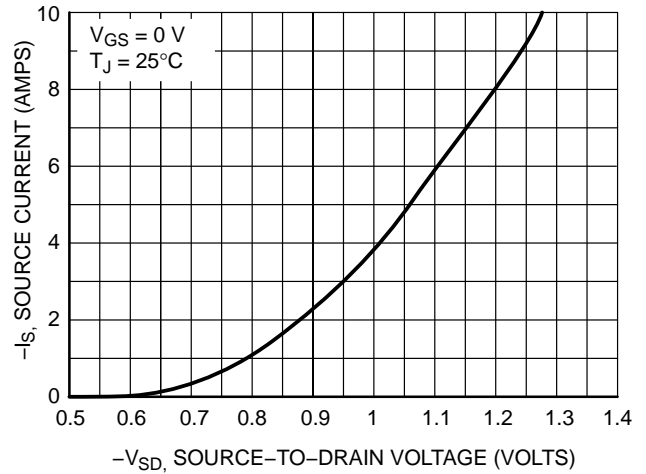
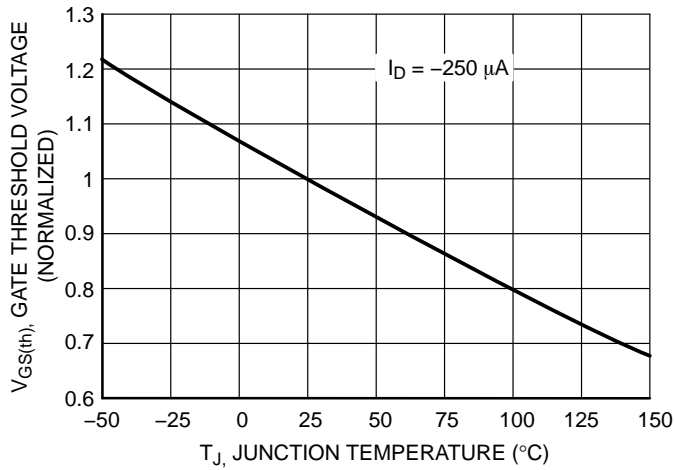
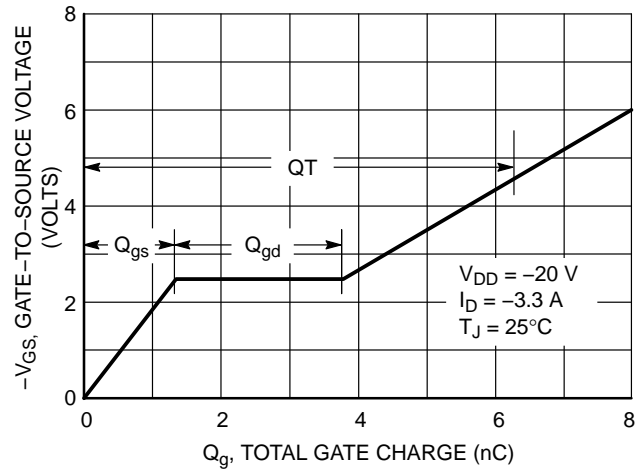
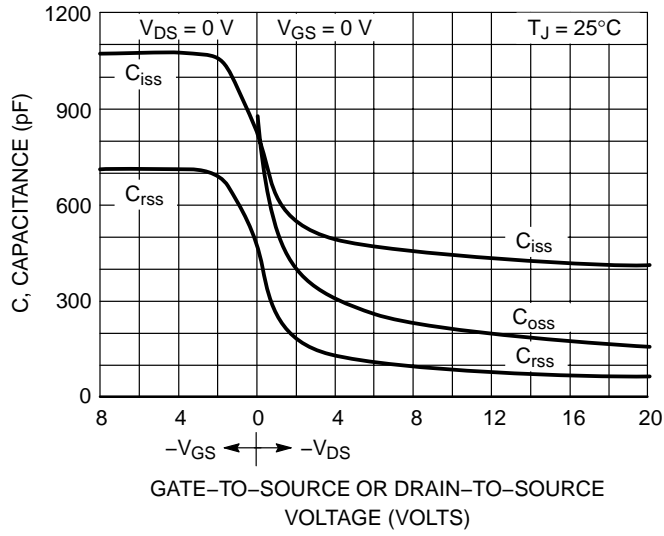


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL ELECTRICAL CHARACTERISTICS



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TYPICAL ELECTRICAL CHARACTERISTICS

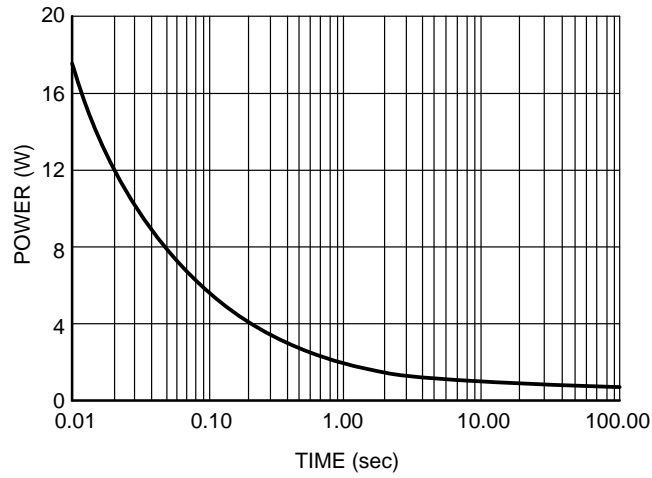


Figure 11. Single Pulse Power

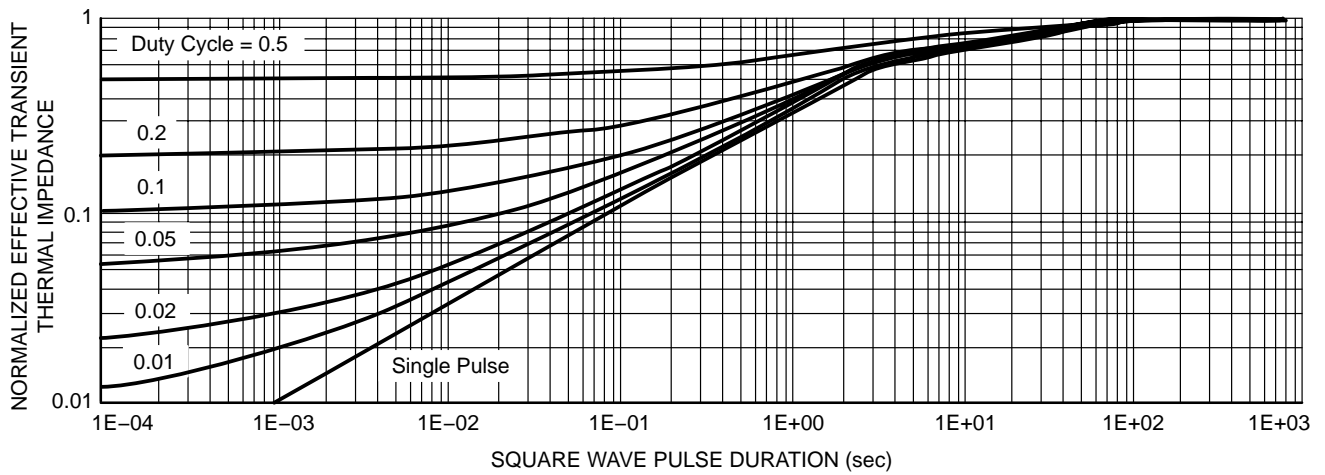
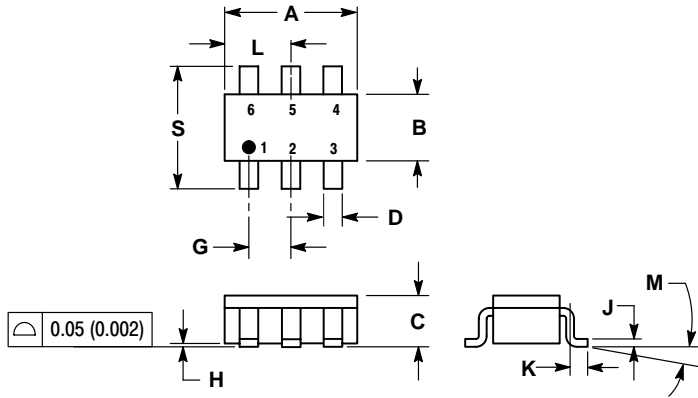


Figure 12. Normalized Thermal Transient Impedance, Junction-to-Ambient

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PACKAGE DIMENSIONS

TSOP-6 CASE 318G-02 ISSUE L



NOTES:

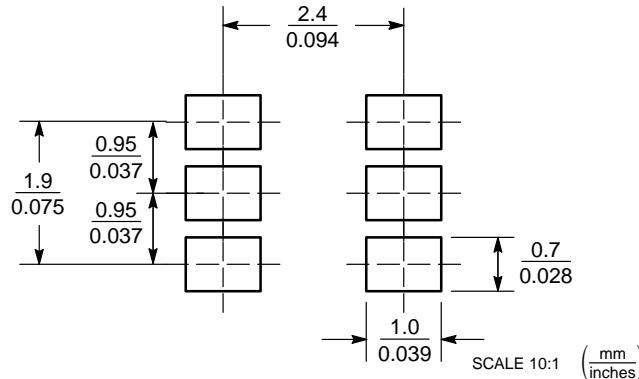
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.90	3.10	0.1142	0.1220
B	1.30	1.70	0.0512	0.0669
C	0.90	1.10	0.0354	0.0433
D	0.25	0.50	0.0098	0.0197
E	0.85	1.05	0.0335	0.0413
F	0.013	0.100	0.0005	0.0040
G	0.10	0.26	0.0040	0.0102
H	0.20	0.60	0.0079	0.0236
I	1.25	1.55	0.0493	0.0610
J	0°	10°	0°	10°
S	2.50	3.00	0.0985	0.1181

STYLE 1:

- PIN 1. DRAIN
- DRAIN
- GATE
- SOURCE
- DRAIN
- DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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